Description

135V N-CHANNEL ENHANCEMENT MODE POWER MOSFET

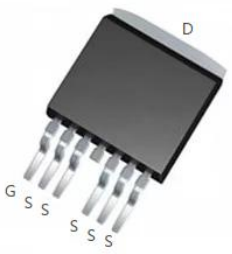
Features

- Device Rating V_{DS} = 135V, I_D = 282A
- $R_{DS(ON)}$ =2.1mΩ (typ.) @ V_{GS} = 10V, I_D = 140A
- Advanced Split Gate Trench Device Design
- RoHS Compliant & Halogen-Free
- Qualified according to JEDEC for target applications
- 100% Avalanche Test

Application

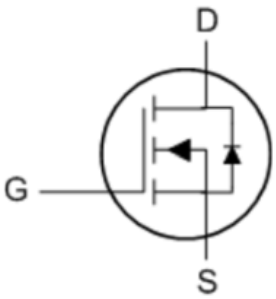
- High Performance Synchronous Rectification
- Brushless DC Motor Control
- Telecom, E-bike, Forklift, Garden tools
- Load Switch and eFuse
- Battery Protection

Package



TO263-7

JFG2R6N135V



Absolute Maximum Ratings T_J=25℃ unless otherwise specified

Symbol	Parameter		Value	Units
V_{DS}	Drain-Source Voltage		135	V
V_{GS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current, VGS @ 10V note1	T_C = 25℃	282	A
		T_C = 100℃	199	A
I_{DM}	Pulsed Drain Current note2		1128	A
P_D	Power Dissipation note4	T_C = 25℃	428	W
	Power Dissipation	T_A = 25℃	3.75	W
E_{AS}	Single Pulsed Avalanche Energy note3		607	mJ
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

Thermal characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case note1	-	0.35	-	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	-	-	40	℃/W

Electrical Characteristics T_J=25℃ unless otherwise specified

Symbol	Parameter	Test Condition		Min.	Typ.	Max.	Units
Off Characteristic							
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA		135	-	-	V
I_{DSS}	Drain-Source Leakage Current	V_{DS} =135V, V_{GS}= 0V, T_C = 25℃		-	-	1	μA
		V_{DS} =135V,V_{GS} = 0V, T_C = 125℃		-	-	100	μA
I_{GSS}	Gate-Source Leakage Current	V_{DS} = 0V, V_{GS} = ±20V		-100	-	100	nA
On Characteristics							
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA		2.5	-	3.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance note2	V_{GS} = 10V, I_D =140A		-	2.1	2.6	mΩ
		V_{GS} = 8V, I_D =70A			2.2	2.7	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 3V, I_D =140A		-	292	-	S
Dynamic Characteristics							
R_g	Gate Resistance	f=1.0MHz		-	0.4	-	Ω
C_{iss}	Input Capacitance	V_{DS} = 68V, V_{GS} = 0V, f = 1.0MHz		-	8758	-	pF
C_{oss}	Output Capacitance			-	1319	-	pF
C_{rss}	Reverse Transfer Capacitance			-	12	-	pF
Q_g	Total Gate Charge	V_{DS} =68V, I_D = 70A, V_{GS} = 10V		-	143	-	nC
Q_{gs}	Gate-Source Charge			-	42	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge			-	38	-	nC
Switching Characteristics							
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 68V, I_D = 70A, R_G = 1Ω, V_{GS} = 10V		-	36	-	ns
t_r	Turn-On Rise Time			-	43	-	ns
$t_{d(off)}$	Turn-Off Delay Time			-	42	-	ns
t_f	Turn-Off Fall Time			-	15	-	ns
Source-Drain Diode Characteristics and Maximum Ratings							
I_S	Maximum Continuous Diode Forward Current note1,5			-	-	282	A
I_{SM}	Maximum Pulsed Diode Forward Current note2,5			-	-	1128	A
t_{rr}	Reverse Recovery Time	V_R = 68V, I_S = 70A, V_{GS} = 0V		-	56	-	ns
Q_{rr}	Reverse Recovery Charge	di/dt = 400A/μs		-	196	-	nC
V_{SD} note2	Diode Forward Voltage	I_S = 140A, V_{GS} = 0V	T_J = 25°C	-	0.85	-	V
			T_J =125°C	-	0.76	-	V

Note :

1.The data tested by surface mounted on one $inch^2$ FR-4 board with 2OZ copper.

2.The data tested by pulsed, pulse width ≦ 300us, duty cycle ≦ 2%.

3.The EAS data shows Max. rating. The test condition is L=0.5mH, I_{AS}= 51A.

4.The power dissipation is limited by 150℃ junction temperature.

5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Performance Characteristics

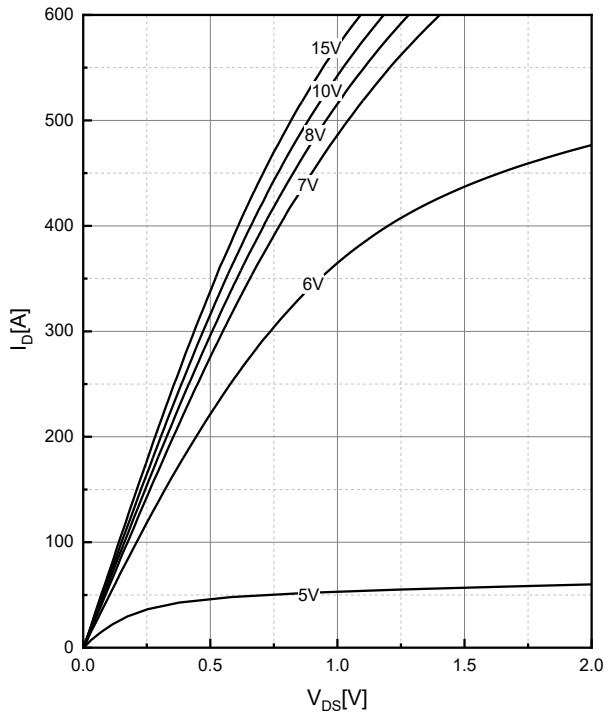


Figure 1. Output Characteristics, T_J=25℃

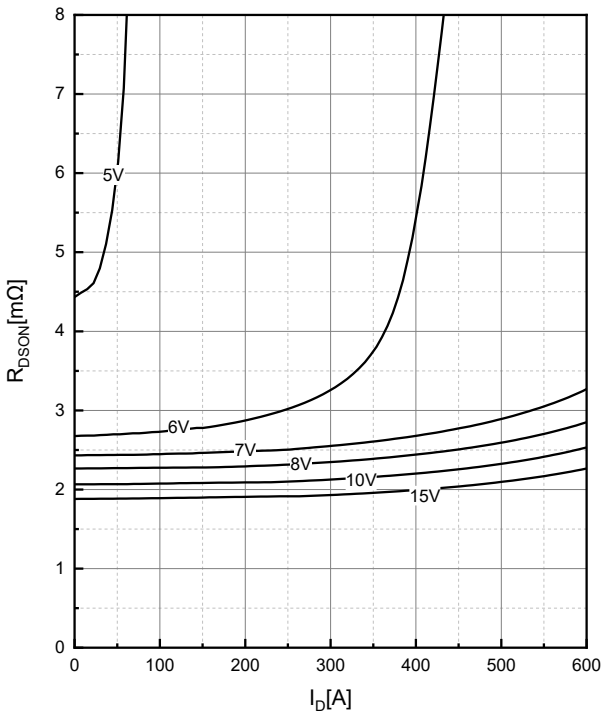


Figure 2. Drain-source on resistance , T_J=25℃

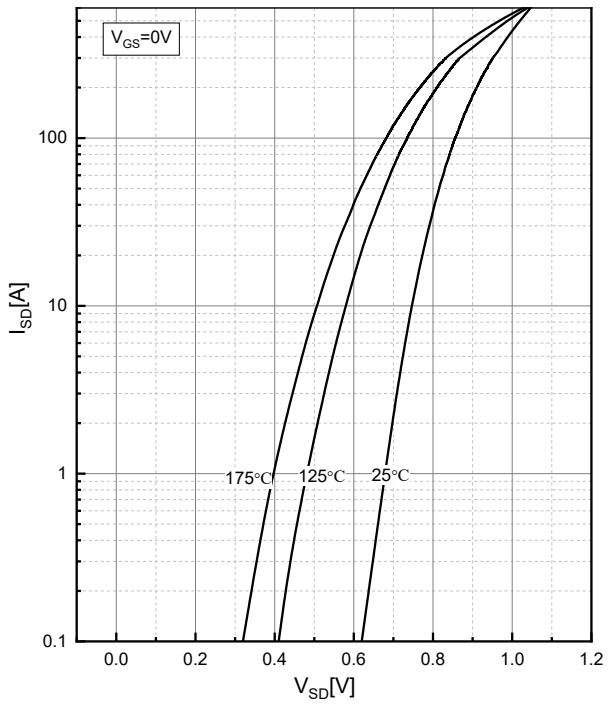


Figure 3. Forward characteristics of body diode

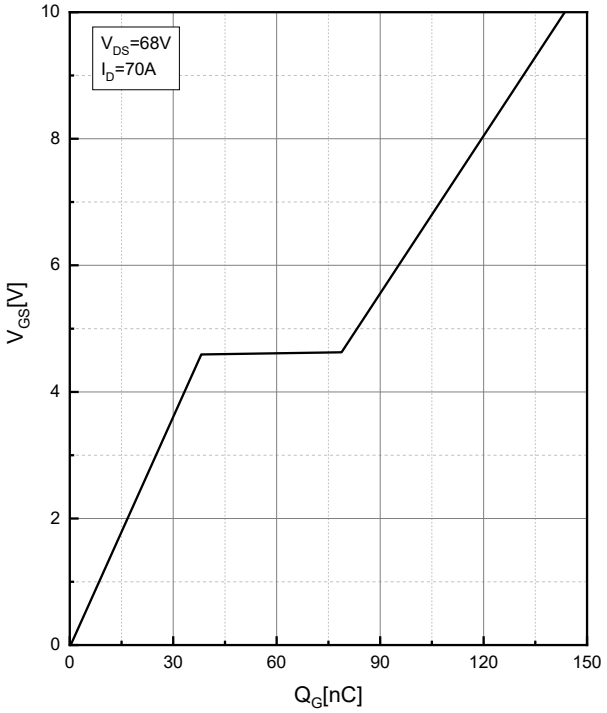


Figure 4. Gate Charge Characteristics

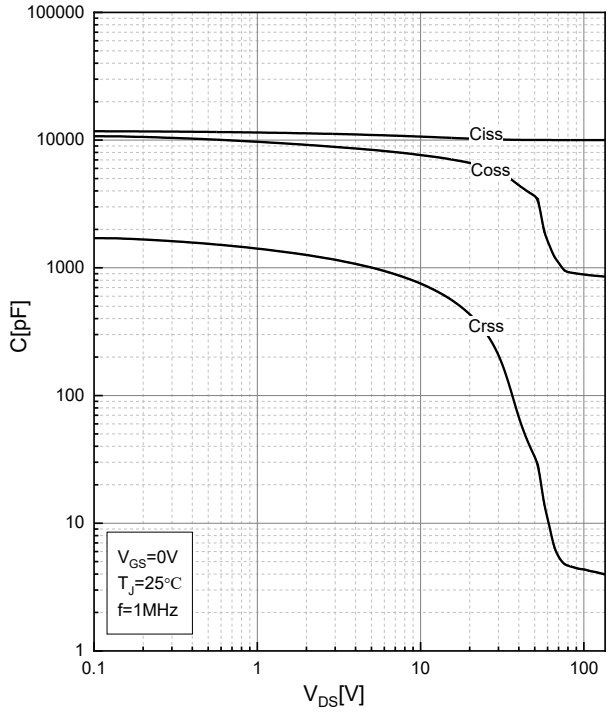


Figure 5. Capacitance Characteristics

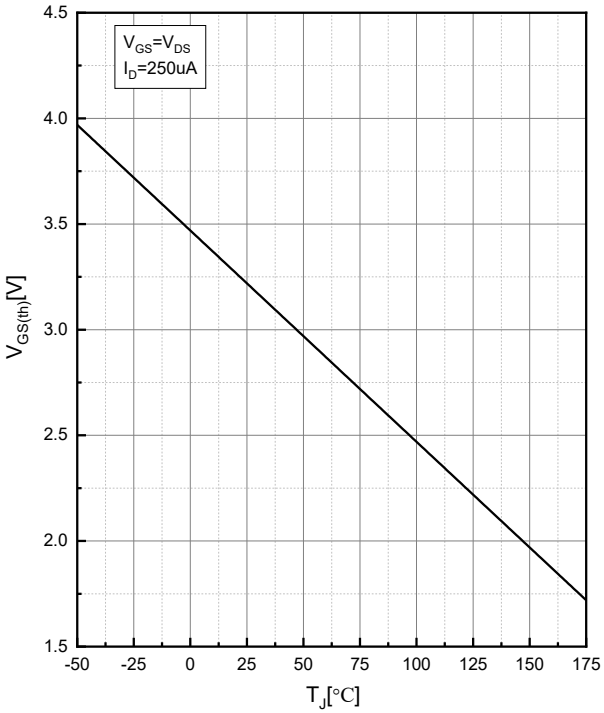


Figure 6. Threshold Voltage Vs. Temperature

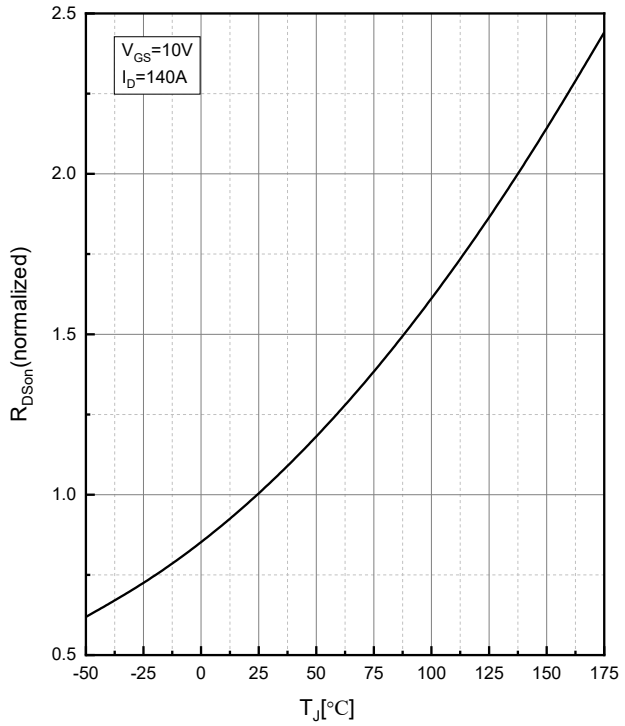


Figure 7. Drain-source on-state resistance

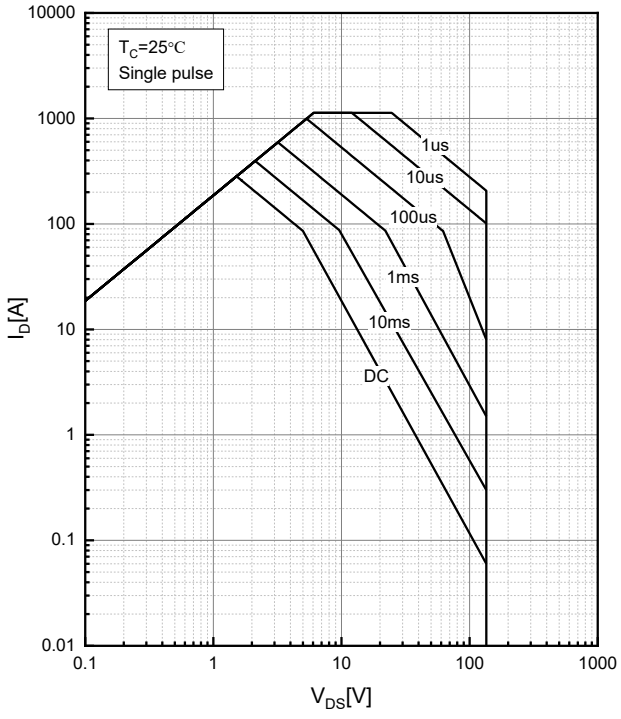


Figure 8. Maximum Safe Operating Area

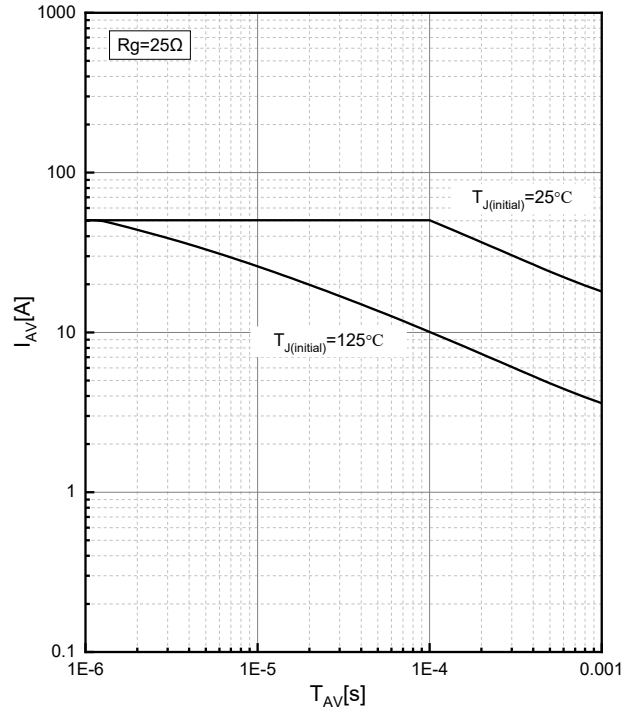


Figure 9. Avalanche characteristics

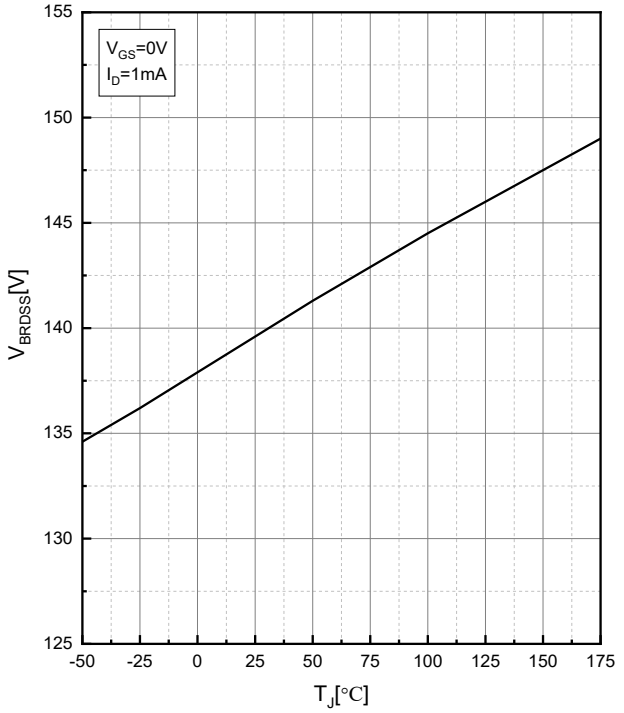


Figure 10. Drain-source breakdown voltage

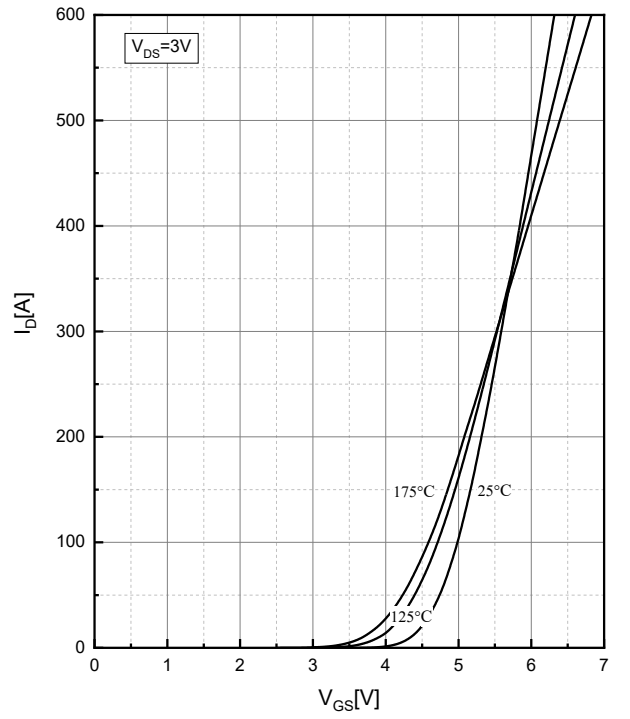


Figure 11. Transfer characteristics

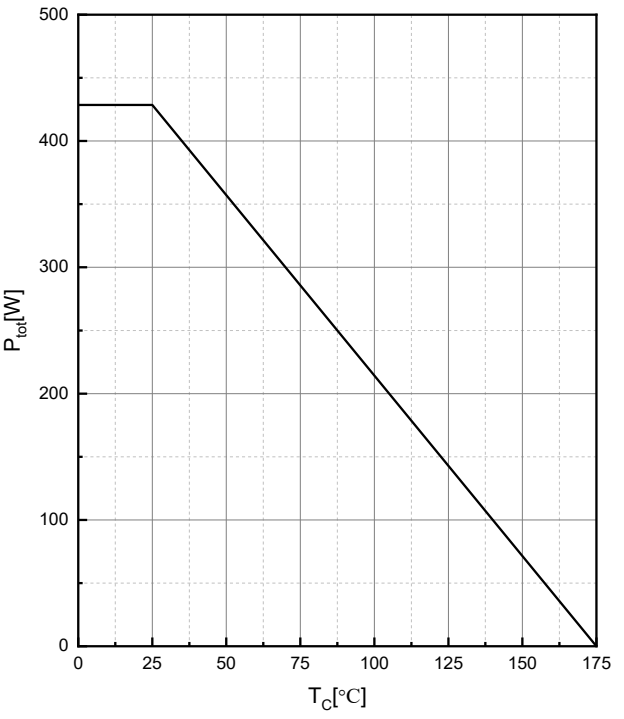


Figure 12. Power dissipation

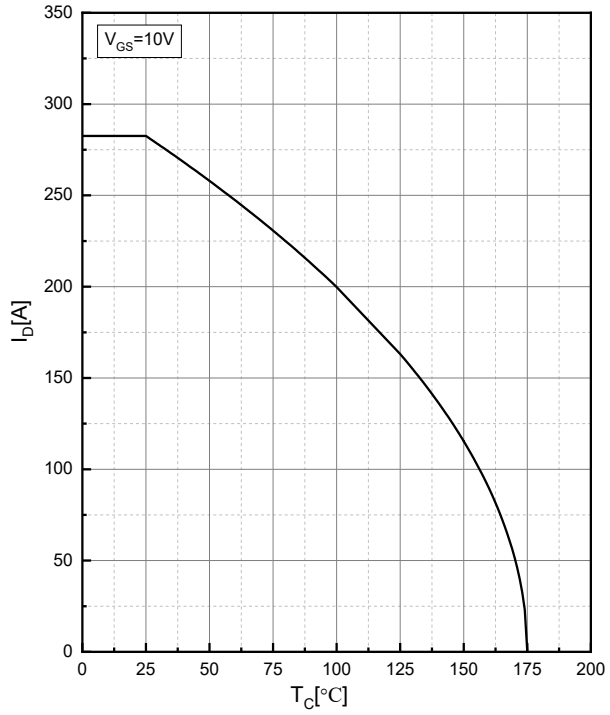


Figure 13. Drain current

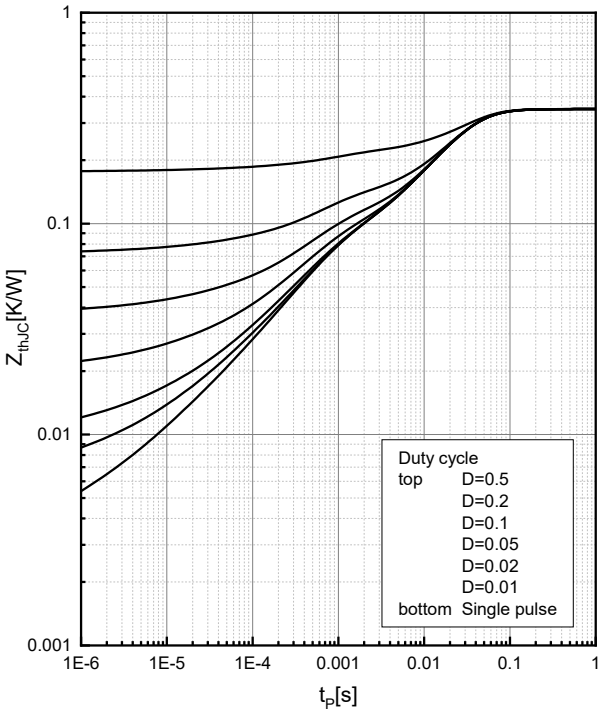


Figure 14. Effective Transient Thermal Impedance

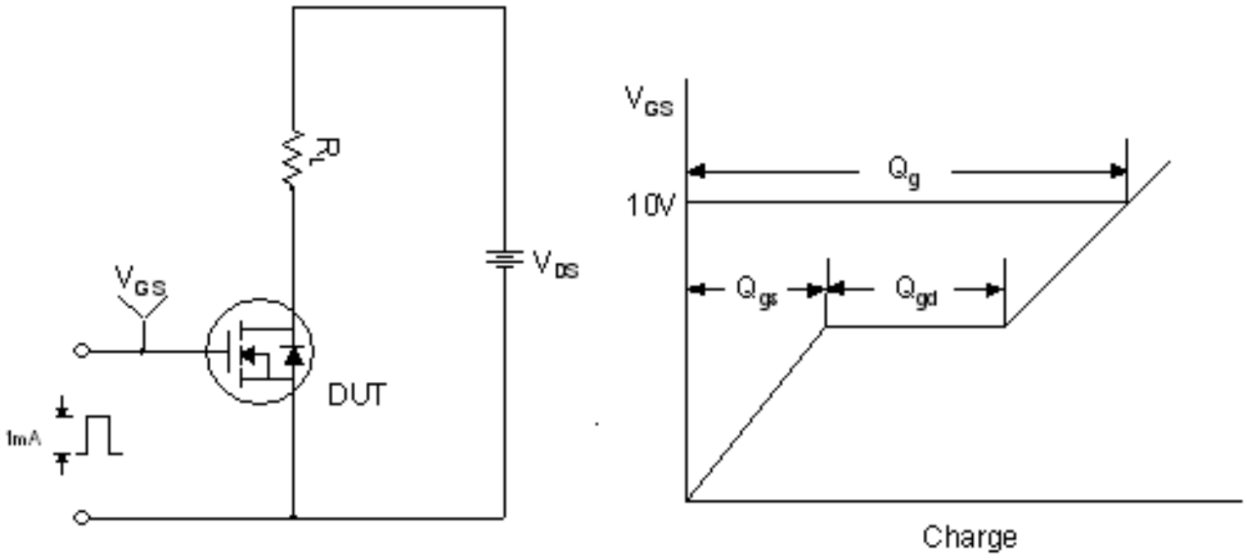


Figure 15. Gate Charge Test Circuit & Waveform

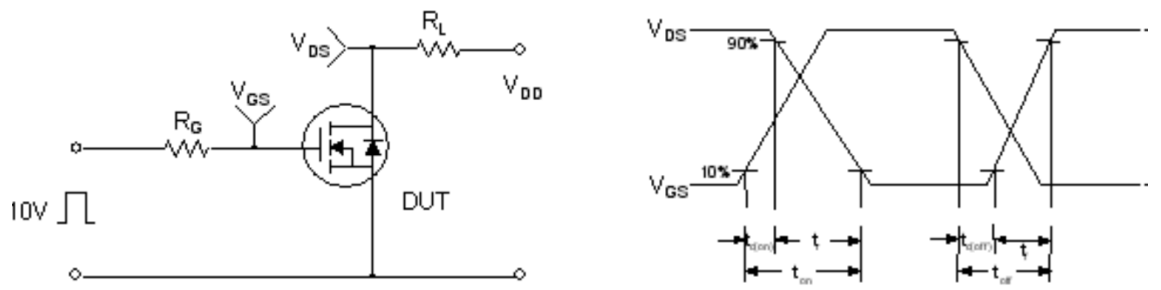


Figure 16. Resistive Switching Test Circuit & Waveforms

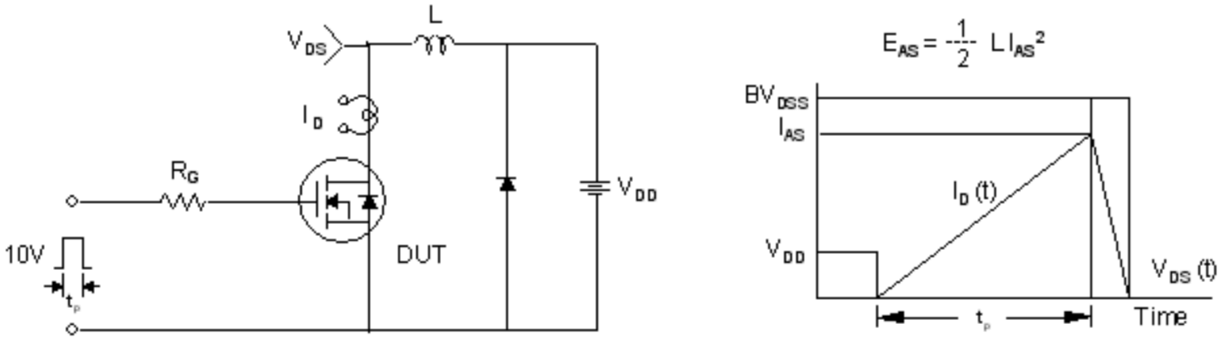


Figure 17. Unclamped Inductive Switching Test Circuit & Waveforms

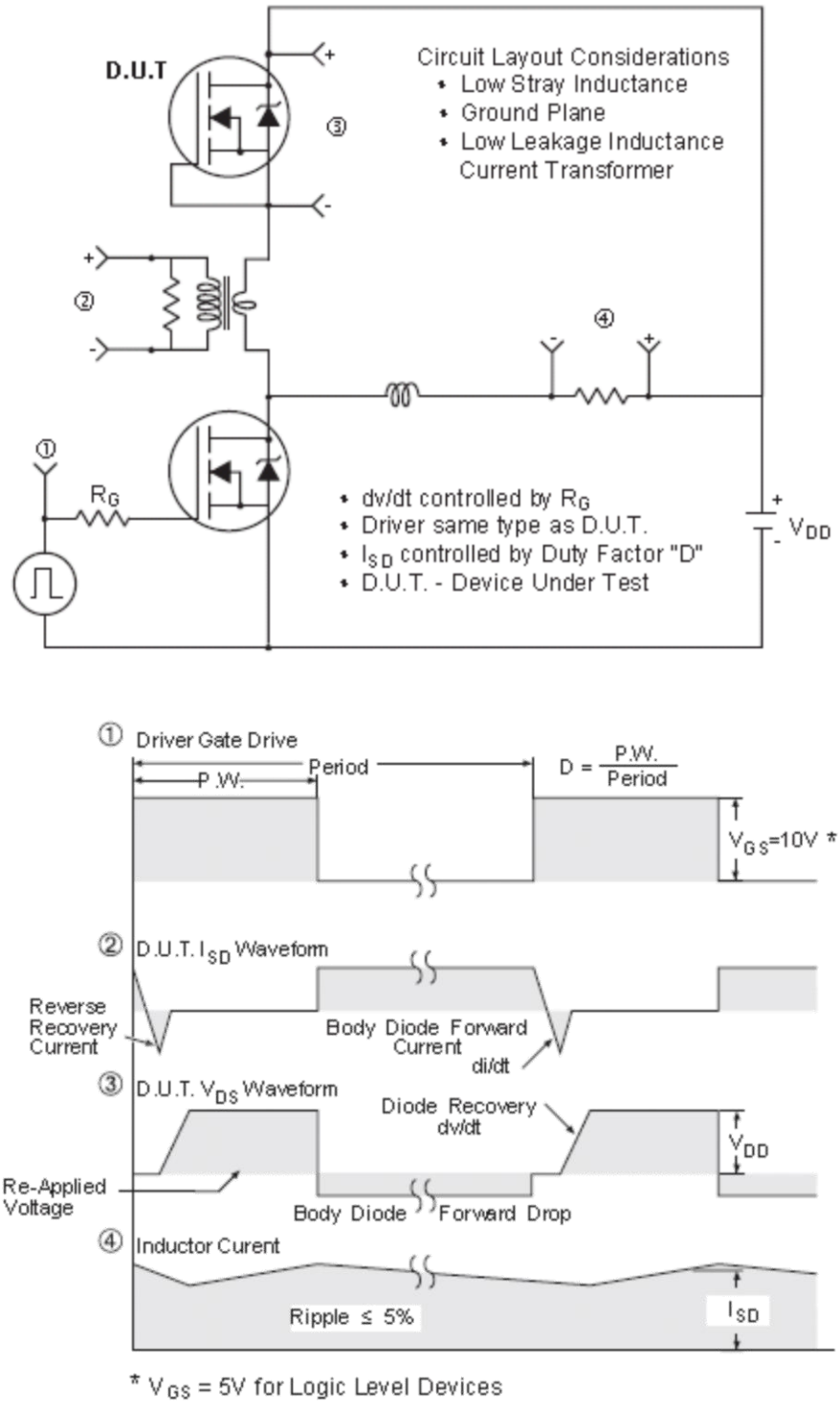
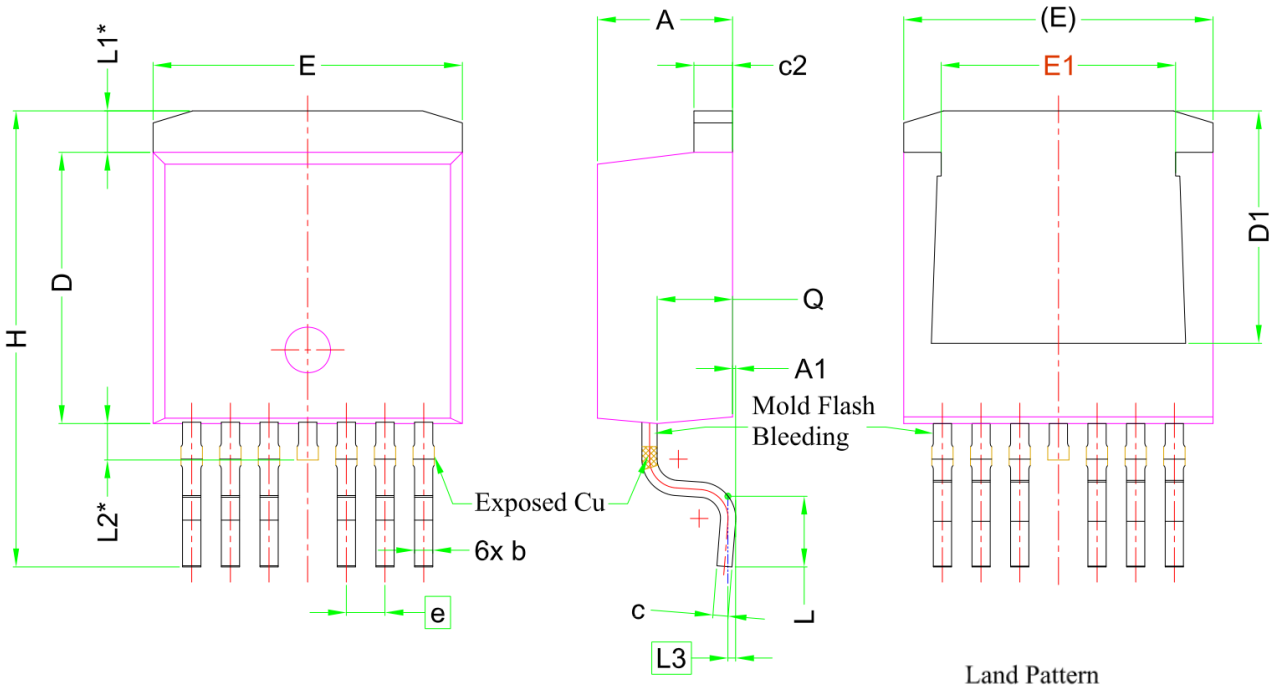
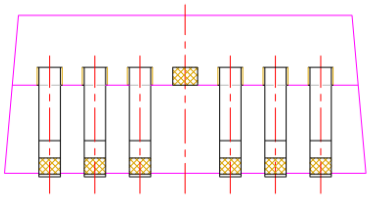


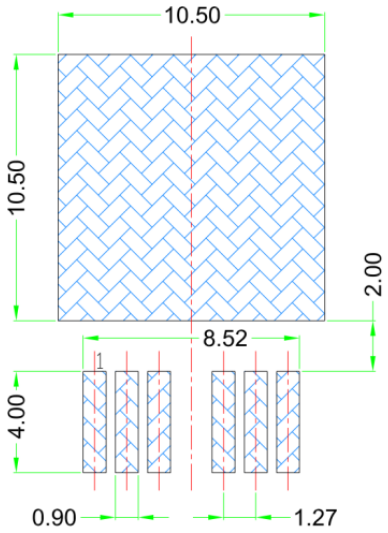
Figure 18. Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

Package outline





Land Pattern
(Only for Reference)



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	---
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.20 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

Note:
1. All Dimensions Are In mm.
2. Dimension D & E Do Not Include Mold Flash.
   Mold Flash Shall Not Exceed 0.127mm Pre Side.
   These Dimensions Are Measured At The Outermost
   Extreme Of The Plastic Body.
3. Thermal Pad Contour Optional Within Dimensions E, L1, D1 & E1.
4. Dimension D1 & E1 Establish A Minmum Mounting Surface for
   The Thermal Pad.
5. "*" is reference .
6. ▨ is Exposed Cu.

Figure 19. TO263-7 Package outline

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